





NPN SURFACE MOUNT TRANSISTOR

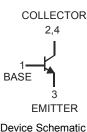
Features

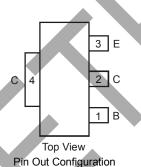
- **Epitaxial Planar Die Construction**
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.055 grams (approximate)







Top View

Device Schematic

Maximum Ratings @TA = 25°C unless otherwise specified

	Characteristic	Symbol	Value	Unit
Collector-Base Voltage		V _{CBO}	30	V
Collector-Emitter Voltage		V _{CEO}	25	V
Emitter-Base Voltage		V_{EBO}	6.0	V
Collector Current		l _C	2.0	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @T _A = 25°C	$R_{ heta JA}$	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

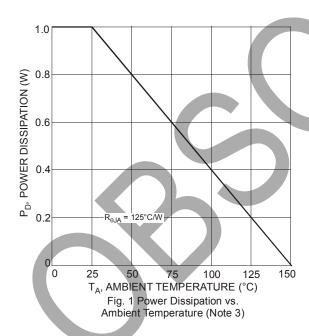
 Device mounted on FR-4 PCB; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

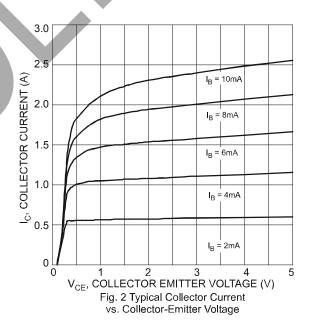


Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	30	_	_	V	$I_C = 10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	25	_	_	V	$I_{C} = 1 \text{mA}, I_{B} = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0	_		V	$I_C = 10\mu A, I_C = 0$
Collector-Base Cutoff Current	I _{CBO}		_	100	nA	$V_{CB} = 20V, I_{E} = 0$
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 4.0V, I_C = 0$
ON CHARACTERISTICS (Note 4)						
DC Current Gain	h	200	_	400		$V_{CE} = 2.0V, I_{C} = 0.1A$
Do Current Gain	h _{FE}	65	_	_		$V_{CE} = 2.0V, I_{C} = 1.5A$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		0.12	0.4	V	$I_C = 1.5A, I_B = 75mA$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$		0.9	1.2	٧	$I_C = 1.5A$, $I_B = 75mA$
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f _T	_	300		MHz	$V_{CE} = 10V, I_{C} = 50mA,$ f = 100MHz
Output Capacitance	C_{obo}	_	16		pF	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$
SWITCHING CHARACTERISTICS						
Turn On Time	t _{on}		70		ns	V - 10V V - 5V
Storage Time	t _{stg}		170		ns	$V_{CE} = 12V, V_{BE} = 5V,$ $I_{B1} = I_{B2} = 25\text{mA}, I_{C} = 500\text{mA}$
Fall Time	t _f		25		ns	181 - 182 - 25IIIA, IC = 500IIIA

Notes: 4. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.







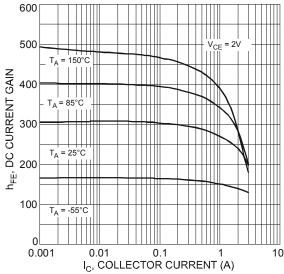


Fig. 3 Typical DC Current Gain vs. Collector Current

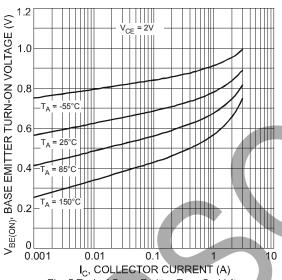


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

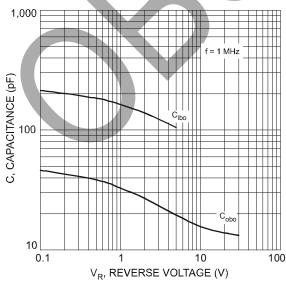


Fig. 7 Typical Junction Capacitance Characteristics

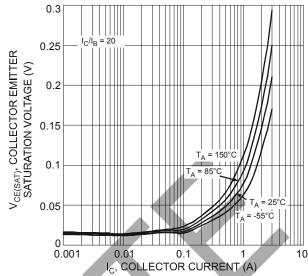


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

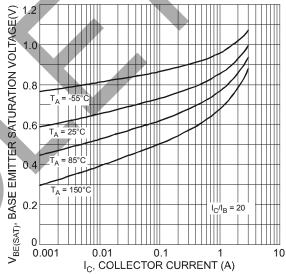


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

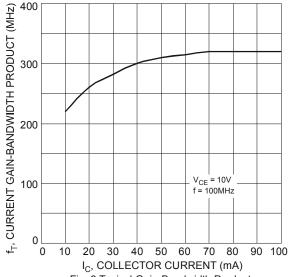


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

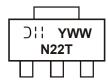


Ordering Information (Note 5)

Part Number	Case	Packaging
2DD1621T-13	SOT89-3L	2500/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



N22T = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year (ex: 7 = 2007) WW = Week code (01 – 53)

SOT89-3L

1.40

0.44

0.35

0.35

4.40

1.52

2.29

3.94 0.89

All Dimensions in mm

Max 1.60

0.62

0.54

0.43

4.60

1.83

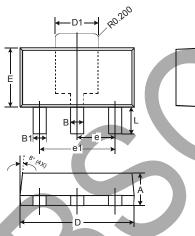
2.60

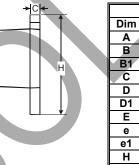
1.20

1.50 Typ

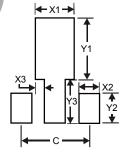
3.00 Typ

Package Outline Dimensions





Suggested Pad Layout



Dimensions	Value (in mm)
X1	1.7
X2	0.9
Х3	0.4
Y1	2.7
Y2	1.3
Y3	1.9
С	3.0



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